UNİSYS

DATE:

December 7, 1994

PPM-95-107

TO:

1 Lohr/3111

FROM:

K. Sahu/300.1 K≤

SUBJECT:

Radiation Report on CASSINI/CIRS

Part No. RP7820 Control No. 11424

cc:

A. Sharma/311

Library/300.1

A radiation evaluation was performed on RP7820 (8-bit Flash A/D Converter) to determine the total dose tolerance of these parts. A brief summary of the test results is provided below. For detailed information, refer to Tables I through IV and Figure 1.

The total dose testing was performed using a ⁶⁰Co gamma ray source. During the radiation testing, eight parts were irradiated under bias (see Figure 1 for bias configuration), and two parts were used as control samples. The total dose radiation levels were 2.5, 5, 10, 15, 20, 30 and 50 krads*. The dose rate was between 0.06 and 1.18 krads/hour, depending on the total dose level (see Table II for radiation schedule). After the 50 krad irradiation, parts were annealed at 25°C for 168 hours, after which the parts were annealed at 100°C for 168 hours. After each radiation exposure and annealing treatment, parts were electrically tested according to the test conditions and the specification limits** listed in Table III.

All parts passed initial electrical measurements. All irradiated parts passed all electrical and functional tests up to and including the 10 krad irradiation level.

At the 15 krad level, S/N 73, 77 and 79 exceeded the maximum specification limit of \pm 3.00 μ A for at least one of eight ioh tests (DB0-DB7), with readings ranging from 3.21 to 5.13 μ A and S/N 76 marginally exceeded the maximum specification limit of \pm 0.25 lsb for PS sens, with a reading of 0.27 lsb. All other parts passed all other electrical tests.

At the 20 krad level, S/N 73, 74, 76, 77, 78 and 79 exceeded the maximum specification limit for various ioh tests, with readings ranging from 3.02 to 5.13 μ A. In addition, S/N 79 exceeded the maximum specification limit of 0.40 V for INT, with a reading of 1.02 V.

At the 30 krad level, all irradiated parts except S/N 75 exceeded the maximum specification limit for at least one ion test and three parts (S/N 73, 77 and 79) exceeded the maximum specification limit for all eight, with readings ranging from 3.13 to 5.13 μ A. In addition, S/N 72 exceeded the maximum specification limit of 0.40 V for INT, with a reading of 1.02 V.

At the 50 krad level, all irradiated parts failed at least one ioh test and five parts (S/N 73, 76, 77, 78 and 79) failed all eight, with readings ranging from 3.22 to 5.13 μ A.

^{*}The term rads, as used in this document, means rads(silicon). All radiation levels cited are cumulative.

^{**}These are manufacturer's pre-irradiation data specification limits. No post-irradiation limits were provided by the manufacturer at the time these tests were performed.

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After annealing for 168 hours at 25°C, no recovery was observed.

After annealing for 168 hours at 100°C, no rebound effects were observed.

Table IV provides a summary of the mean and standard deviation values for each parameter after different irradiation exposures and annealing steps.

Any further details about this evaluation can be obtained upon request. If you have any questions, please call me at (301) 731-8954.

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TABLE I. Part Information

Generic Part Number:

RP7820

CASSINI/CIRS

Part Number:

RP7820

CASSINI/CIRS

Control Number:

11424

Charge Number:

EE44542

Manufacturer:

Space Electronics, Inc.

Lot Date Code:

9234

Quantity Tested:

10

Serial Number of

Control Samples:

70, 71

Serial Numbers of

Radiation Samples:

72, 73, 74, 75, 76, 77, 78, 79

Part Function:

8-bit Flash A/D Converter

Part Technology:

High-Speed CMOS

Package Style:

20-pin DIP

Test Equipment:

A540

Test Engineer:

C. Nguyen

^{*} No radiation tolerance/hardness was guaranteed by the manufacturer for this part.

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TABLE H. Radiation Schedule for RP7820

EVENT		DATE
I) INITIAL ELECTRICAL MEASUR	EMENTS	10/03/94
2) 2.5 KRAD IRRADIATION (0.15 K POST-2.5 KRAD ELECTRICAL MEA	KRADS/HOUR) ASUREMENT	10/05/94
3) 5 KRAD IRRADIATION (0.15 KR	ADS/HOUR)	10/06/94
POST-5 KRAD ELECTRICAL MEAS		10/07/94
4) 10 KRAD IRRADIATION (0.06 KI	RADS/HOUR)	10/07/94
POST-10 KRAD ELECTRICAL MEA	SUREMENT	10/11/94
5) 15 KRAD IRRADIATION (0.29 KF	RADS/HOUR)	10/11/94
POST-15 KRAD ELECTRICAL MEAS	SUREMENT	10/12/94
6) 20 KRAD IRRADIATION (0.29 KE	RADS/HOUR)	10/12/94
POST-20 KRAD ELECTRICAL MEAS	SUREMENT	10/13/94
7) 30 KRAD IRRADIATION (0.15 KF	RADS/HOUR)	10/14/94
POST-30 KRAD ELECTRICAL MEAS	SUREMENT	10/17/94
8) 50 KRAD IRRADIATION (1,18 KR	RADS/HOUR)	10/17/94
POST-50 KRAD ELECTRICAL MEAS	SUREMENT	10/18/94
9) 168-HOUR ANNEALING @25°C POST-168 HOUR ANNEAL ELECTRI	CAL MEASUREMENT	10/18/94 10/25/94
10) 168-HOUR ANNEALING @100°C	**	10/25/94
POST-168 HOUR ANNEAL ELECTRI	CAL MEASUREMENT	11/01/94

PARTS WERE IRRADIATED AND ANNEALED UNDER BIAS; SEE FIGURE 1.

^{*}High temperature annealing is performed to accelerate long term time dependent effects (TDE), namely, the "rebound" effect due to the growth of interface states after the radiation exposure. For more information on the need to perform this test, refer to MIL-STD-883D, Method 1019, Para. 3.10.1. -4'-

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Table III. Electrical Characteristics of RP7820

Test temperature : 25oC

tst 	Test name	Min	Мах	Condition
1	ICC	0.00 ma	16.00 ma	CS = RD = 0v
2	DB7 voh	2.40 v		iout =-0.36ma
3	DB6 voh	2,40 v		*
4	DB5 voh	2.40 v		
5	DB4 voh	2.40 v		
6	DB3 voh	2.40 v		•
7	DB2 voh	2.40 v		
8	DB1 voh	2.40 v		•
9	DB0 voh	2.40 v		*
10	INT voh	2.40 v		
11	OFL voh	2.40 v		, "
12	DB7 vol		0.40 v	iout = 1.6ma
13	DB6 vol		0.40 v	•
14	DB5 vol		0.40 - v	*
15	DB4 vol		0.40 v	H
16	DB3 vol		0.40 v	•
17	DB2 vol ·		0.40 v	•
18	DB1 vol		0.40 v	•
19	DB0 vol		0.49 v	•
20	INT vol		0.40 v	
21	OFL vol		0.40 V	•
22	PS sens	-0.25 ls	0.25 lsb(*)	
23	CS_iih	-0.00 ua	1.00 ua	vil=0.6v vih=2.4v
24	WR_iih	-0.00 ua	3.00 ua	•
25	RD iih	-0.0 Oua	1.00 ua	•
26	CS_iil	-1.0 ua	0.00 ua	•
27	WR_iil	-1.0 ua	0.00 ua	•
28	RD_iil	1.0 ua	0.00 ua	
29	MODE_iih	0.0 ua	200.00 ua(*)	vil=1.5v vih=3.5v
30	MODB_iil	-1.0 ua	1.00 ua	*
31	DE7 ioh	-3.00 ua	3.00 ua	vl=0.0v vh=5.0v
32	DB6 ioh	-3.00 ua	3.00 ua	•
33	DB5 ioh	-3.00 ua	3.00 ua	•
34	DB4 ich	-3.00 ua	3.00 ца	•
35	DB3 ioh	-3.00 ua	3.00 ua	•
36	DB2 ioh	-3.00 ua	3.00 ua	•

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Table III (cont'd.). Electrical Characteristics of RP7820

37	DBL ich	-3.00 ua	3.00 ua	*
38	DBO ich	-3.00 ua	3.00 ua	
39	DB7 io1	-3.00 ua	3,00 ua	
40	DB6 iol	-3.00 ua	3.00 ua	u
41	DBS iol	-3.00 ua	3.00 ua	
42	DB4 iol	-3.00 ua	3,00 ua	
4.3	DB3 iol	3.00 ua	3.00 ua	
44	DB2 iol	-3.00 ua	3.00 ua	-
45	DB1 iol	-3.00 ua	3.00 ua	-
46	DB0 iol	-3.00 ua	3.00 ua	•
			**	
47	Vin iih	-3.00 ua	3.00 ua	
48	Vin iil	-3.00 ua	3.00 ua	*
		*****	D	
49	Rof. Resist	600,0 ohms	1500.0 ohms	
50	Missing codes		0.000	
51	TUE	-1.000 lsb	1.000 lsb	
52	tc_WR/RD	0.00 us	1.38 us	WR/RD mode
53	t intl	0.0 ns	100 0 ns	mit, ide mode

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TABLE IV: Summary of Electrical Measurements after Total Dose Exposures and Annealing for RP7820 /1

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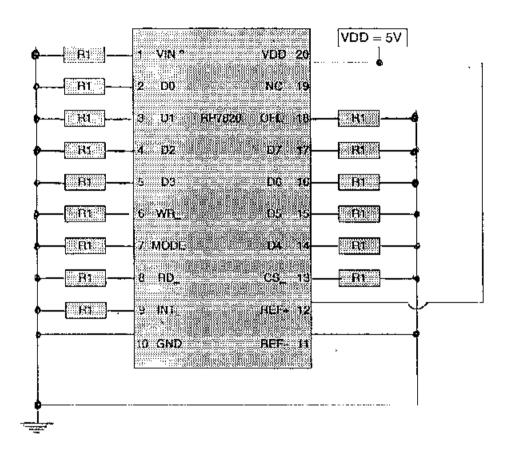
The mean and standard deviation values were calculated over the eight parts irradiated in this testing. The control samples remained constant throughout the testing and are not included in this table.

These are manufacturer's non-irradiated data sheet specification limits. No post-irradiation limits were provided by the manufacturer at the time the tests were performed.

Radiation-sensitive parameters: ioh, PS sens and INT. _

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Figure 1. Radiation Bias Circuit for RP7820



R1 2K to 47K, 1/4W Min. ±